



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

44-10 / EXT /  
2 / AMOR B  
4-1-03  
VS

In re the Application of:

)

OKU et al

)

Examiner: Dang, T.

)

Serial No.: 09/903,764

)

Art Unit: 2823

)

Filed: July 13, 2001

)

)

For: FILM FORMING METHOD, SEMICONDUCTOR

)

DEVICE AND SEMICONDUCTOR DEVICE

)

MANUFACTURING METHOD

)

RESPONSE TO OFFICE ACTION OF OCTOBER 24, 2002

Assistant Commissioner for Patents

Washington, D.C. 20231

Sir:

Responsive to the office action of October 24, 2002, please amend the captioned application as follows:

RECEIVED  
MAR 23 2003  
U.S. PATENT AND TRADEMARK OFFICE

RECEIVED  
MAR 23 2003  
U.S. PATENT AND TRADEMARK OFFICE

IN THE CLAIMS:

Please cancel claims 6 and 7 and rewrite claims 1-5 and 8 as follows:

1. (Amended) A film forming method for forming a silicon-containing barrier insulating film on a substrate comprising the steps of:

(a) preparing a film-forming gas comprising, (1) at least one member selected from the group consisting of alkoxy compounds having Si-H bonds and siloxane compounds having Si-H